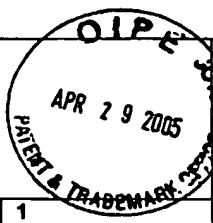


Substitute form 1449A/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Sheet 1 of 1



Complete if Known

Application Number	10/698,170
Filing Date	October 30, 2003
First Named Inventor	Sei-Hyung Ryu
Group Art Unit	2811
Examiner Name	Tran, Long K.
Attorney Docket Number	5308-279

**U.S. PATENTS AND PATENT PUBLICATIONS**

Examiner Initials*	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code (if known)		
LT	1	6,303,508	B1	Alok	10/2001
	2	6,297,100	B1	Kumar et al.	10/2001
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LT	20	WO	97/08754			03/1997	

**OTHER NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
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Examiner Signature

/Long Tran/

Date Considered

05/05/2006

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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<b>FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office</b>				<b>Attorney Docket Number:</b> 5308-279		<b>Serial No.:</b> 10/698,170	
<b>LIST OF DOCUMENTS CITED BY APPLICANT</b> (Use several sheets if necessary)				<b>Applicants:</b> Sei-Hyung Ryu			
				<b>Filing Date:</b> October 30, 2003		<b>Group</b> 2811	
<b>U. S. PATENT DOCUMENTS</b>							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
LT	1.	6,204,135	03/20/2001	Peters et al.	438	301	
<b>FOREIGN PATENT DOCUMENTS</b>							
		Document Number	Date	Country	Class	Subclass	Translation Yes   No
LT	2.	DE 198 32 329	2/4/1999	Germany	H01L	21/334	
LT	3.	WO 01/78134	10/18/2001	PCT	H01L	21/76	
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							

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<b>LIST OF DOCUMENTS CITED BY APPLICANT</b> (Use several sheets if necessary)							
Applicants: Sei-Hyung Ryu							
Filing Date: October 30, 2003						Group 281	
<b>U. S. PATENT DOCUMENTS</b>							
Examiner Initial	1.	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
LT		6,429,041	08/06/2002	Ryu et al.	438	105	
<b>FOREIGN PATENT DOCUMENTS</b>							
		Document Number	Date	Country	Class	Subclass	Translation Yes   No
LT	2.	JP 03034466	02/14/1991	Japan			Abstract
LT	3.	JP 01117363	05/10/1989	Japan			Abstract
LT	4.	EP 1058317 A2	12/06/2000	EPO			
LT	5.	DE 19809554 A1	09/10/1998	Germany			
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
LT	6.	Copy of International Search Report for PCT/US03/38490 mailed 08/05/2004					

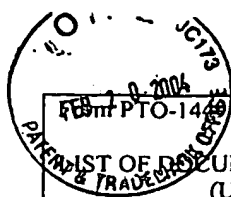
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LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)		Applicant: Sei-Hyung Ryu	
		Filing Date: October 30, 2003	GAU: 2811

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	2	6,316,791	11/13/01	Schorner et al.	257	77	
	3	6,228,720	05/08/01	Kitabatake et al.	438	268	
	4	5,877,045	3/2/99	Kapoor	438	151	
	5	5,739,564	4/14/98	Kosa et al.	257	298	
	6	5,587,870	12/24/96	Anderson et al.	361	313	
	7	5,479,316	12/26/95	Smrtic et al.	361	322	
	8	2002/0102358	8/1/02	Das et al.	472	376.2	10/26/01
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LT	10	2002/0038891	4/4/02	Ryu et al.	257	350	6/24/01

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LT	11	WO99/63591	12/9/99	PCT			
LT	12	WO 98/02924	01/22/98	PCT			
LT	13	WO 00/13236	03/09/00	PCT			

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	17	United States Provisional Patent Application Serial No. 60/294,307
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	19	Mutin, P. Herbert, "Control of the Composition and Structure of Silicon Oxycarbide and Oxynitride Glasses Derived from Polysiloxane Precursors," <i>Journal of Sol-Gel Science and Technology</i> , Vol. 14 (1999) pp. 27-38.
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Examiner:

/Long Tran/

Date Considered: 05/05/2006

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Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<b>FORM PTO-1449 U.S. Department of Commerce</b> Patent and Trademark Office  <b>LIST OF DOCUMENTS CITED BY APPLICANT</b>  (Use several sheets if necessary)				Attorney Docket Number: 5308-279		Serial No.: To Be Assigned <div style="text-align: right; font-size: 1.2em;">10/698170</div>	
				Applicants: Sei-Hyung Ryu			
				Filing Date: Concurrently Herewith		Group Unknown 2878	

U. S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
UKT	1	6,593,620	7/15/03	Hsieh et al.	257	335	
	2	6,455,892	9/02	Okuno	257	77	
	3	6,344,663 B1	2/5/02	Slater, Jr. et al.	257	77	
	4	6,297,172	10/2/01	Kashiwagi	438	773	
	5	6,246,076 B1	6/12/01	Lipkin et al.	257	77	
	6	6,239,463	5/29/01	Williams et al.	257	328	
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	8	6,221,700	4/24/01	Okuno et al.	438	151	
	9	6,211,035	4/01	Moise et al.	438	396	
	10	6,204,203	3/01	Narwanker et al.	438	785	
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	13	6,136,728	10/24/00	Wang			
	14	6,117,735	9/12/00	Ueno	438	268	
	15	6,107,142	8/22/00	Suvorov et al.	438	285	
	16	6,100,169	8/8/00	Suvorov et al.	438	519	
	17	6,096,607	8/1/00	Ueno	438	522	
	18	6,063,698	5/16/00	Tseng et al.			
	19	6,054,352	4/25/00	Ueno	438	268	
	20	6,048,766	4/11/00	Gardner et al.			
	21	6,028,012	2/22/00	Wang			
W	22	6,025,608	2/15/00	Harris et al.	257	77	
UKT	23	5,972,801	10/26/99	Lipkin et al.	438	770	
	24	<del>5,972,801</del>	<del>10/26/99</del>	<del>Lipkin et al.</del>	438	770	
UKT	25	5,960,289	9/28/99	Tsui et al.	438	257	
UKT	26	5,939,763	8/17/99	Hao et al.	257	411	
UKT	27	5,885,870A	3/99	Maiti et al.	438	261	

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					<b>Applicants:</b> Sei-Hyung Ryu			
					<b>Filing Date:</b> Concurrently Herewith		<b>Group</b> Unknown <div style="font-size: 1.2em; font-family: cursive;">2878</div>	

<div style="font-size: 1.5em; font-family: cursive;">W</div>	28	5,837,572	11/17/98	Gardner et al.	438	199	
	29	5,763,905	6/9/98	Harris	257	77	
	30	5,726,463	3/10/98	Brown et al.	257	77	
	31	5,510,630	4/23/96	Agarwal	257	77	
	32	5,506,421	4-9-96	Palmour	257	77	
	33	5,184,199	2/2/93	Fujii et al.	29	10	
	34	5,170,455	12/8/92	Goossen et al.	385	89	
	35	5,170,231	12/92	Fujii et al.	257	77	
	36	4,875,083	10/17/89	Palmour	357	23.6	
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	38	3,924,024	12/2/75	Naber et al.	427	95	
	39	2002/0072247	6/13/02	Lipkin et al.	438	767	
<div style="font-size: 1.5em; font-family: cursive;">W</div>	40	2001/0055852	12/01	Moise et al.	438	396	

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	<div style="font-size: 1.5em; font-family: cursive;">W</div>	41	0637069 A1/ B1	2/1/95	EPO		
		42	DE 10036208	2/14/02	Germany		Abstract
		43	DE 198 09 554	9/10/98	Germany		Abstract
		44	DE 19900171	12/26/00	Germany		Abstract
		45	JP 03157974	7/5/91	Japan		Abstract
		46	JP 08264766	10/11/96	Japan		Abstract
		47	JP 09205202	8/5/97	Japan		Abstract
		48	JP 11191559	7/13/99	Japan		Abstract
		49	JP 11238742	8/31/99	Japan		Abstract
		50	JP 11261061	9/24/99	Japan		Abstract
		51	JP 11266017	9/28/99	Japan		Abstract
		52	JP 11274487	10/8/99	Japan		Abstract
		53	JP 2000049167	2/18/00	Japan		Abstract
	<div style="font-size: 1.5em; font-family: cursive;">W</div>	54	JP 2000082812	3/21/00	Japan		Abstract

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LIST OF DOCUMENTS CITED BY APPLICANT  (Use several sheets if necessary)					Applicants: Sei-Hyung Ryu			
					Filing Date: Concurrently Herewith			Group <del>Unknown</del> <b>2828</b>
<b>UET</b>	55	JP 2000106371	4/11/01	Japan				Abstract
	56	JP0200025246	9/14/00	Japan				Abstract
	57	WO 97/17730	5/15/97	PCT				
<b>UET</b>	58	WO 97/39485	10/23/97	PCT				
59 OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)								
<b>UET</b>	59	A.K. Agarwal, J.B. Casady, L.B. Rowland, W.F. Valek, and C.D. Brandt, "1400 V 4H-SiC Power MOSFET's," <i>Materials Science Forum</i> Vols. 264-268, pp.989-992, 1998.						
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<b>UET</b>	73	Das, Mrinal K. Graduate thesis entitled, <i>Fundamental Studies of the Silicon Carbide MOS Structure</i> . Purdue University, 1999.						

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LIST OF DOCUMENTS CITED BY APPLICANT  (Use several sheets if necessary)		Applicants: Sei-Hyung Ryu	
		Filing Date: Concurrently Herewith	Group Unknown 2818
✓	74	Fukuda et al. "Improvement of SiO <sub>2</sub> /4H-SiC Interface Using High-Temperature Hydrogen Annealing at Low Pressure and Vacuum Annealing," <i>Jpn J. Appl. Phys.</i> Vol. 38, April 1999, pp. 2306-9	
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FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office		Attorney Docket Number: 5308-279	Serial No.: To Be Assigned  10/698 170
LIST OF DOCUMENTS CITED BY APPLICANT  (Use several sheets if necessary)		Applicants: Sei-Hyung Ryu	
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<b>FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office</b>  <b>LIST OF DOCUMENTS CITED BY APPLICANT</b>  (Use several sheets if necessary)		<b>Attorney Docket Number:</b> 5308-279	<b>Serial No.:</b> To Be Assigned  10/698770
		<b>Applicants:</b> Sei-Hyung Ryu	
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